

# **NHDTC114/124/144ET series**

80 V, 100 mA NPN resistor-equipped transistors

Rev. 1 — 26 June 2020

**Product data sheet** 

## 1. General description

NPN Resistor-Equipped Transistor (RET) family in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

**Table 1. Product overview** 

Type number	R1	R2		Package	PNP complement:
	kΩ	kΩ	Nexperia	JEDEC	
NHDTC114ET	10	10	SOT23	TO-236AB	NHDTA114ET
NHDTC124ET	22	22			NHDTA124ET
NHDTC144ET	47	47			NHDTA144ET

## 2. Features and benefits

- · 100 mA output current capability
- High breakdown voltage
- · Built-in resistors
- · Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

# 3. Applications

- · Digital applications
- · Cost saving alternative for BC846 series in digital applications
- Controlling IC inputs
- Switching loads

## 4. Quick reference data

#### Table 2. Quick reference data

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	80	V
Io	output current		-	-	100	mA



# 5. Pinning information

#### **Table 3. Pinning**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)	<u></u> 3	
2	GND	GND (emitter)		R1
3	0	output (collector)		
				GND
			1	aaa-019964

# 6. Ordering information

### **Table 4. Ordering information**

Type number	Package						
	Name	Description	Version				
NHDTC114ET	TO-236AB	plastic surface-mounted package; 3 leads	SOT23				
NHDTC124ET							
NHDTC144ET							

# 7. Marking

### Table 5. Marking

Table 5. Marking					
Type number	Marking code [1]				
NHDTC114ET	QG%				
NHDTC124ET	QK%				
NHDTC144ET	QM%				

[1] % = placeholder for manufacturing site code

# 8. Limiting values

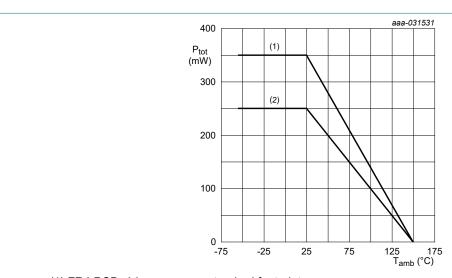
#### **Table 6. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

T<sub>amb</sub> = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Max	Unit	
V <sub>CBO</sub>	collector-base voltage	open emitter		-	80	V	
V <sub>CEO</sub>	collector-emitter voltage	open base		-	80	V	
V <sub>EBO</sub>	emitter-base voltage	open collector		-	10	V	
VI	input voltage						
	NHDTC114ET			-10	+40	V	
	NHDTC124ET			-10	+60	V	
	NHDTC144ET			-10	+80	V	
Io	output current			-	100	mA	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	250	mW	
			[2]	-	350	mW	
Tj	junction temperature			-	150	°C	
T <sub>amb</sub>	ambient temperature			-55	150	°C	
T <sub>stg</sub>	storage temperature			-65	150	°C	

- [1] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit-Board (PCB);4-layer copper; tin-plated and standard footprint.



- (1) FR4 PCB, 4-layer copper, standard footprint
- (2) FR4 PCB, single-sided copper, standard footprint

Fig. 1. Power derating curves for SOT23 (TO-236AB)

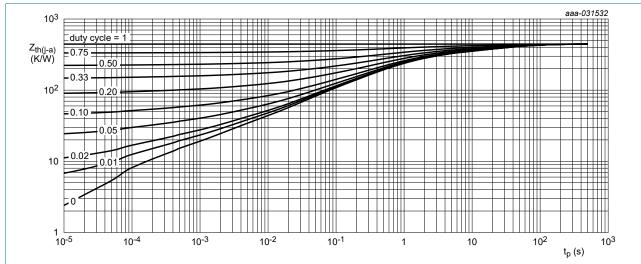
### 9. Thermal characteristics

#### **Table 7. Thermal characteristics**

 $T_{amb}$  = 25 °C unless otherwise specified.

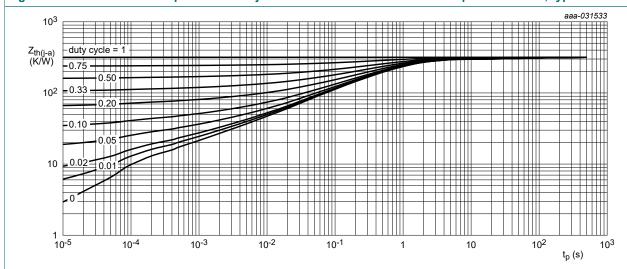
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W
			[2]	-	-	358	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	130	K/W

- [1] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated and standard footprint.



FR4 PCB, single-sided copper, tin-plated and standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, tin-plated and standard footprint

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

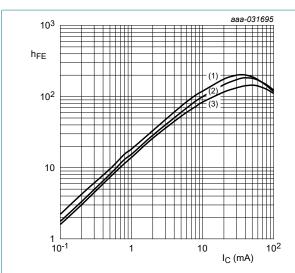
#### **Table 8. Characteristics**

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	I <sub>C</sub> = 100 μA; I <sub>E</sub> = 0 A		80	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}$		80	-	-	V
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 80 V; I <sub>E</sub> = 0 A		-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off	V <sub>CE</sub> = 60 V; I <sub>B</sub> = 0 A		-	-	100	nA
	current	V <sub>CE</sub> = 60 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	5	μΑ
I <sub>EBO</sub>	emitter-base cut-off curr	ent					
	NHDTC114ET	V <sub>EB</sub> = 7 V; I <sub>C</sub> = 0 A		-	-	600	μΑ
	NHDTC124ET			-	-	270	μΑ
	NHDTC144ET	-			-	130	μΑ
h <sub>FE</sub>	DC current gain					_	
	NHDTC114ET	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$			-	-	
	NHDTC124ET			70	-	-	
	NHDTC144ET				-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA		-	-	100	mV
V <sub>I(off)</sub>	off-state input voltage	V <sub>CE</sub> = 5 V ; I <sub>C</sub> = 100 μA		-	1.15	0.8	V
V <sub>I(on)</sub>	on-state input voltage						
	NHDTC114ET	V <sub>CE</sub> = 0.3 V ; I <sub>C</sub> = 10 mA		2.5	1.8	-	V
	NHDTC124ET			3	2.3	-	V
	NHDTC144ET			5	3.3	-	V
R1	bias resistor 1 (input)	bias resistor 1 (input) [1]					
	NHDTC114ET		'	7	10	13	kΩ
	NHDTC124ET			15.4	22	28.6	kΩ
	NHDTC144ET			33	47	61	kΩ
R2/R1	bias resitor ratio		[1]	0.8	1	1.2	
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 10 mA; f = 100 MHz	[2]	-	170	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = i <sub>e</sub> = 0 A; f = 1 MHz		-	-	2.5	pF

<sup>[1]</sup> See section "Test information" for resistor calculation and test conditions

<sup>[2]</sup> Characteristics of built-in transistor



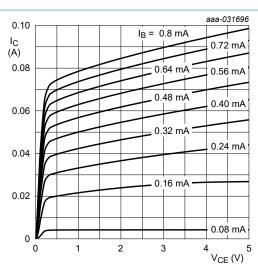
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

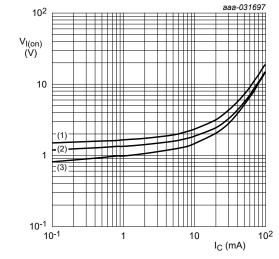
(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 4. NHDTC114ET: DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

Fig. 5. NHDTC114ET: Collector current as a function of collector-emitter voltage; typical values



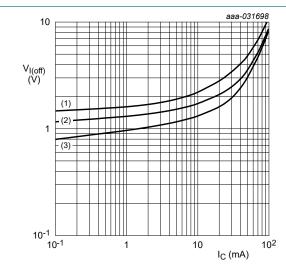
 $V_{CE} = 0.3 V$ 

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. NHDTC114ET: On-state input voltage as a function of collector current; typical values



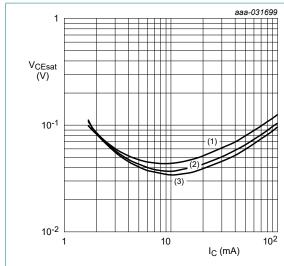
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -40$$
 °C

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. NHDTC114ET: Off-state input voltage as a function of collector current; typical values



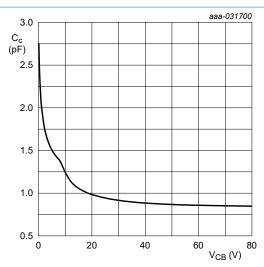
 $I_C/I_B = 20$ 

(1)  $T_{amb}$  = 100 °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

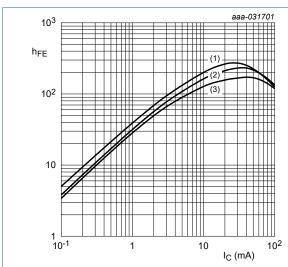
Fig. 8. NHDTC114ET: Collector-emitter saturation voltage as a function of collector current; typical values



f = 1 MHz

T<sub>amb</sub> = 25 °C

Fig. 9. NHDTC114ET: Collector capacitance as a function of collector-base voltage; typical values



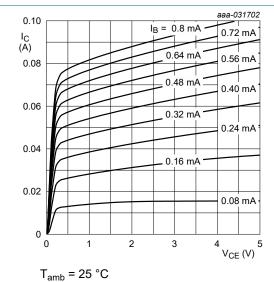
 $V_{CE} = 5 V$ 

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

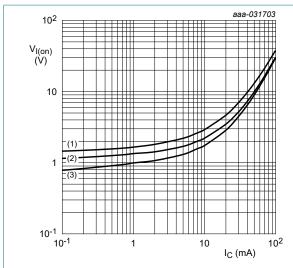
(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 10. NHDTC124ET: DC current gain as a function of collector current; typical values



and

Fig. 11. NHDTC124ET: Collector current as a function of collector-emitter voltage; typical values



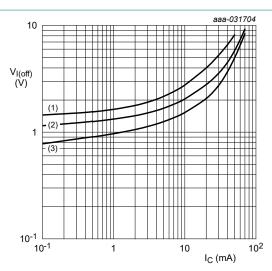
$$V_{CE} = 0.3 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb}$$
 = 100 °C

Fig. 12. NHDTC124ET: On-state input voltage as a function of collector current; typical values



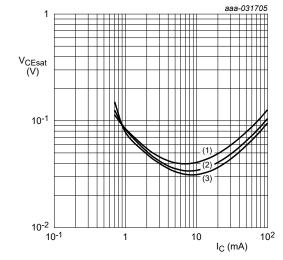
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 13. NHDTC124ET: Off-state input voltage as a function of collector current; typical values



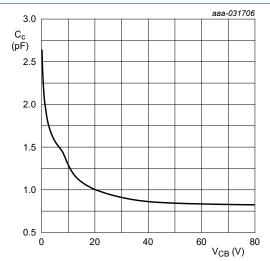
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

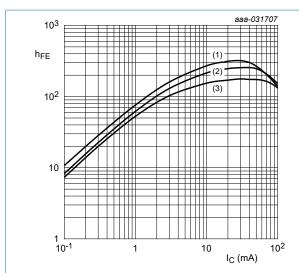
(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 14. NHDTC124ET: Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

Fig. 15. NHDTC124ET: Collector capacitance as a function of collector-base voltage; typical values



$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 16. NHDTC144ET: DC current gain as a function of collector current; typical values

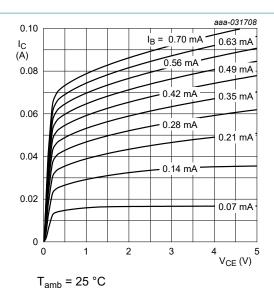
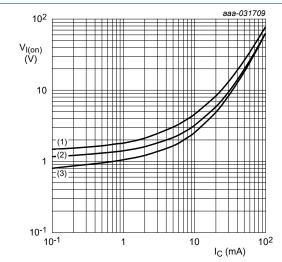


Fig. 17. NHDTC144ET: Collector current as a function of collector-emitter voltage; typical values



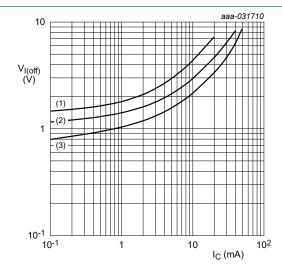
 $V_{CE} = 0.3 V$ 

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 18. NHDTC144ET: On-state input voltage as a function of collector current; typical values



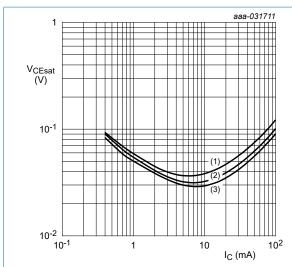
 $V_{CE} = 5 V$ 

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 19. NHDTC144ET: Off-state input voltage as a function of collector current; typical values



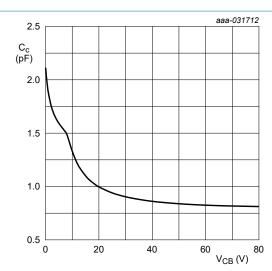
 $I_{\rm C}/I_{\rm B} = 20$ 

(1) T<sub>amb</sub> = 100 °C

(2)  $T_{amb}$  = 25 °C

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

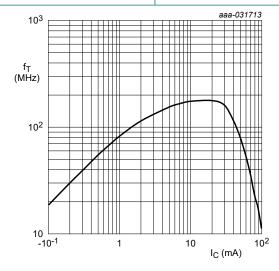
Fig. 20. NHDTC144ET: Collector-emitter saturation voltage as a function of collector current; typical values



f = 1 MHz

T<sub>amb</sub> = 25 °C

Fig. 21. NHDTC144ET: Collector capacitance as a function of collector-base voltage; typical values



f = 100 MHz

 $V_{CE} = 5 V$ 

T<sub>amb</sub> = 25 °C

Fig. 22. Transition frequency as a function of collector current; typical values of built-in transistor

## 11. Test information

### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

#### **Resistor calculation**

Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

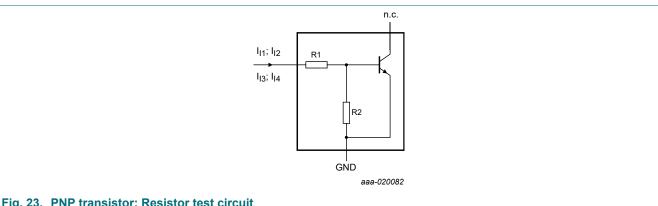


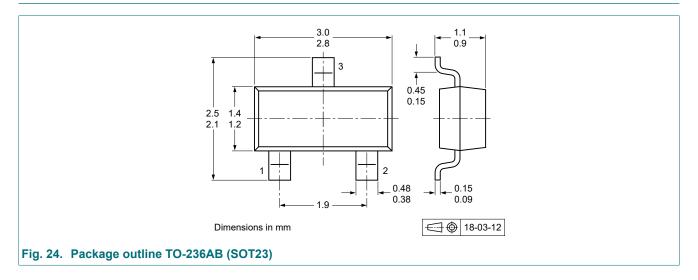
Fig. 23. PNP transistor: Resistor test circuit

### **Resistor test conditions**

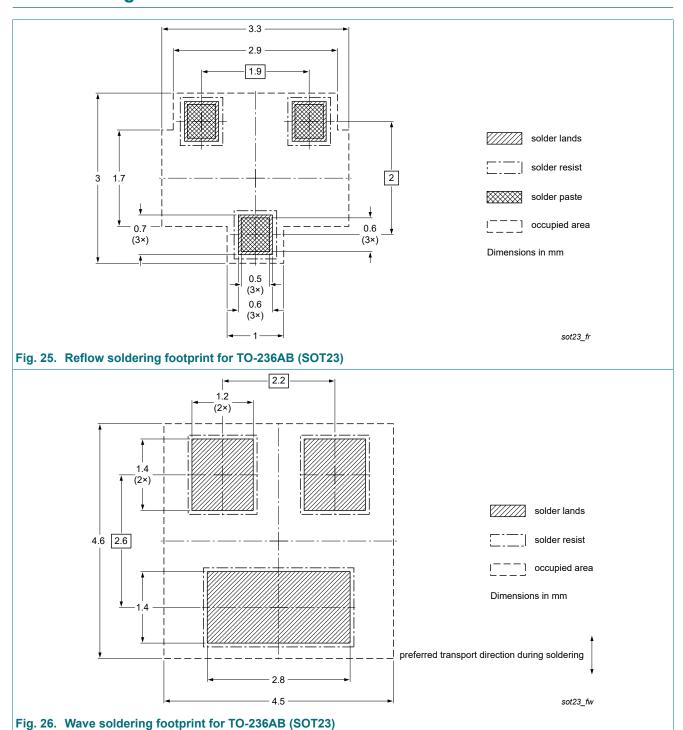
Table 9. Resistor test conditions

Type number	R1 (kΩ)	R2 (kΩ)	Test conditions					Test conditions	
			I <sub>11</sub>	I <sub>12</sub>	I <sub>13</sub>	I <sub>14</sub>			
NHDTC114ET	10	10	800 μΑ	1.1 mA	-350 μΑ	-450 μA			
NHDTC124ET	22	22	550 µA	750 µA	-150 μA	-230 µA			
NHDTC144ET	47	47	250 μΑ	350 μΑ	-55 μΑ	-105 μA			

# 12. Package outline



# 13. Soldering



# 14. Revision history

### Table 10. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NHDTC114_124_144ET_SER v.1	20200626	Product data sheet	-	-

# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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NSBC114YF3T5G NSBC123TF3T5G SMUN5235T1G SMUN5330DW1T1G SSVMUN5312DW1T2G RN1303(TE85L,F)

RN4605(TE85L,F) TTEPROTOTYPE79 DDTC114EUAQ-7-F EMH15T2R SMUN2214T3G SMUN5335DW1T1G NSBC114TF3T5G

NSBC143ZPDP6T5G NSVMUN5113DW1T3G SMUN5230DW1T1G SMUN5133T1G SMUN2214T1G DTC114EUA-TP

NSBA144EF3T5G NSVDTA114EET1G 2SC2223-T1B-A 2SC3912-TB-E SMUN5237DW1T1G SMUN5213DW1T1G

SMUN5114DW1T1G SMUN2111T1G NSVDTC144EM3T5G DTC124ECA-TP DTC123TM3T5G DTA114ECA-TP DTA113EM3T5G

DCX115EK-7-F DTC113EM3T5G NSVMUN5135DW1T1G NSVMUN2237T1G